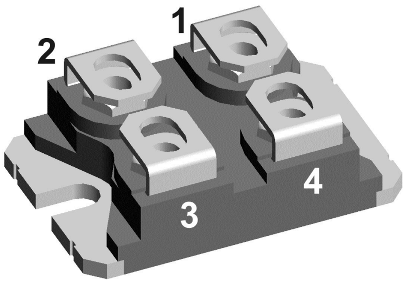
Thyristor

V_{RRM} = 1200 V
I_{TAV} = 80 A
V_T = 1.27 V

Single Thyristor

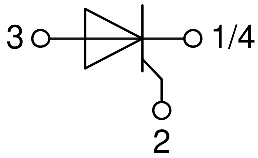
Part number

MCO75-12io1



Backside: isolated

E72873



Features / Advantages:

- Thyristor for line frequency
- Planar passivated chip
- Long-term stability

Applications:

- Line rectifying 50/60 Hz
- Softstart AC motor control
- DC Motor control
- Power converter
- AC power control
- Lighting and temperature control

Package: SOT-227B (minibloc)

- Isolation Voltage: 3000 V~
- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0
- Base plate: Copper internally DCB isolated
- Advanced power cycling

Thyristor

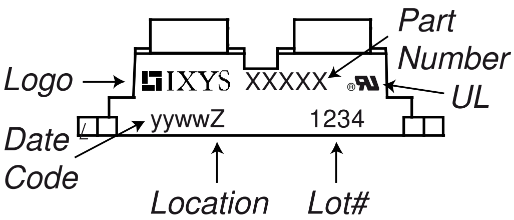
Symbol	Definition	Conditions		Ratings min.	typ.	max.	Unit
$V_{RSM/DSM}$	*max. non-repetitive reverse/forward blocking voltage*		T_{VJ} = 25°C			1300	V
$V_{RRM/DRM}$	*max. repetitive reverse/forward blocking voltage*		T_{VJ} = 25°C			1200	V
$I_{R/D}$	*reverse current, drain current*	$V_{R/D}$ = 1200 V	T_{VJ} = 25°C			50	µA
		$V_{R/D}$ = 1200 V	T_{VJ} = 125°C			10	mA
V_T	*forward voltage drop*	I_T = 75 A	T_{VJ} = 25°C			1.28	V
		I_T = 150 A				1.60	V
		I_T = 75 A	T_{VJ} = 125°C			1.27	V
		I_T = 150 A				1.67	V
I_{TAV}	*average forward current*	T_C = 80°C	T_{VJ} = 150°C			80	A
$I_{T(RMS)}$	*RMS forward current*	180° sine				125	A
V_{T0}	*threshold voltage* } *for power loss calculation only*		T_{VJ} = 150°C			0.85	V
r_T	*slope resistance*					5.5	mΩ
R_{thJC}	*thermal resistance junction to case*					0.45	K/W
R_{thCH}	*thermal resistance case to heatsink*				0.1		K/W
P_{tot}	*total power dissipation*		T_C = 25°C			270	W
I_{TSM}	*max. forward surge current*	t = 10 ms; (50 Hz), sine	T_{VJ} = 45°C			1.07	kA
		t = 8,3 ms; (60 Hz), sine	V_R = 0 V			1.16	kA
		t = 10 ms; (50 Hz), sine	T_{VJ} = 150°C			910	A
		t = 8,3 ms; (60 Hz), sine	V_R = 0 V			980	A
I^2t	*value for fusing*	t = 10 ms; (50 Hz), sine	T_{VJ} = 45°C			5.73	kA^2s
		t = 8,3 ms; (60 Hz), sine	V_R = 0 V			5.55	kA^2s
		t = 10 ms; (50 Hz), sine	T_{VJ} = 150°C			4.14	kA^2s
		t = 8,3 ms; (60 Hz), sine	V_R = 0 V			4.00	kA^2s
C_J	*junction capacitance*	V_R = 400 V f = 1 MHz	T_{VJ} = 25°C		54		pF
P_{GM}	*max. gate power dissipation*	t_P = 30 µs	T_C = 150°C			10	W
		t_P = 300 µs				5	W
P_{GAV}	*average gate power dissipation*					0.5	W
$(di/dt)_{cr}$	*critical rate of rise of current*	T_{VJ} = 150 °C; f = 50 Hz	repetitive, I_T = 225 A			150	A/µs
		t_P = 200 µs; di_G/dt = 0.3 A/µs;					
		I_G = 0.3 A; V = ⅔ V_{DRM}	non-repet., I_T = 75 A			500	A/µs
$(dv/dt)_{cr}$	*critical rate of rise of voltage*	V = ⅔ V_{DRM}	T_{VJ} = 150°C			1000	V/µs
		R_{GK} = ∞; method 1 (linear voltage rise)					
V_{GT}	*gate trigger voltage*	V_D = 6 V	T_{VJ} = 25°C			1.5	V
			T_{VJ} = -40°C			1.6	V
I_{GT}	*gate trigger current*	V_D = 6 V	T_{VJ} = 25°C			100	mA
			T_{VJ} = -40°C			200	mA
V_{GD}	*gate non-trigger voltage*	V_D = ⅔ V_{DRM}	T_{VJ} = 150°C			0.2	V
I_{GD}	*gate non-trigger current*					10	mA
I_L	*latching current*	t_p = 10 µs	T_{VJ} = 25°C			450	mA
		I_G = 0.3 A; di_G/dt = 0.3 A/µs					
I_H	*holding current*	V_D = 6 V R_{GK} = ∞	T_{VJ} = 25°C			200	mA
t_{gd}	*gate controlled delay time*	V_D = ½ V_{DRM}	T_{VJ} = 25°C			2	µs
		I_G = 0.3 A; di_G/dt = 0.3 A/µs					
t_q	*turn-off time*	V_R = 100 V; I_T = 75A; V = ⅔ V_{DRM}	T_{VJ} = 125 °C		150		µs
		di/dt = 10 A/µs dv/dt = 15 V/µs	t_p = 200 µs				

Package SOT-227B (minibloc)

Symbol	Definition	Conditions			Ratings min.	typ.	max.	Unit
I_{RMS}	*RMS current*	per terminal 1)					150	A
T_{VJ}	*virtual junction temperature*				-40		150	°C
T_{op}	*operation temperature*				-40		125	°C
T_{stg}	*storage temperature*				-40		150	°C
Weight						30		g
M_D	*mounting torque*				1.1		1.5	Nm
M_T	*terminal torque*				1.1		1.5	Nm
$d_{Spp/App}$	*creepage distance on surface | striking distance through air*		*terminal to terminal*	10.5	3.2			mm
$d_{Spb/Apb}$			*terminal to backside*	8.6	6.8			mm
V_{ISOL}	*isolation voltage*	t = 1 second	50/60 Hz, RMS; $I_{ISOL} \leq 1$ mA		3000			V
		t = 1 minute			2500			V

1) I_{RMS} is typically limited by the pin-to-chip resistance (1); or by the current capability of the chip (2). In case of (1) and a product with multiple pins for one chip-potential, the current capability can be increased by connecting the pins as one contact.

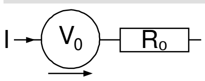
Product Marking



Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	MCO75-12io1	MCO75-12io1	Tube	10	505515

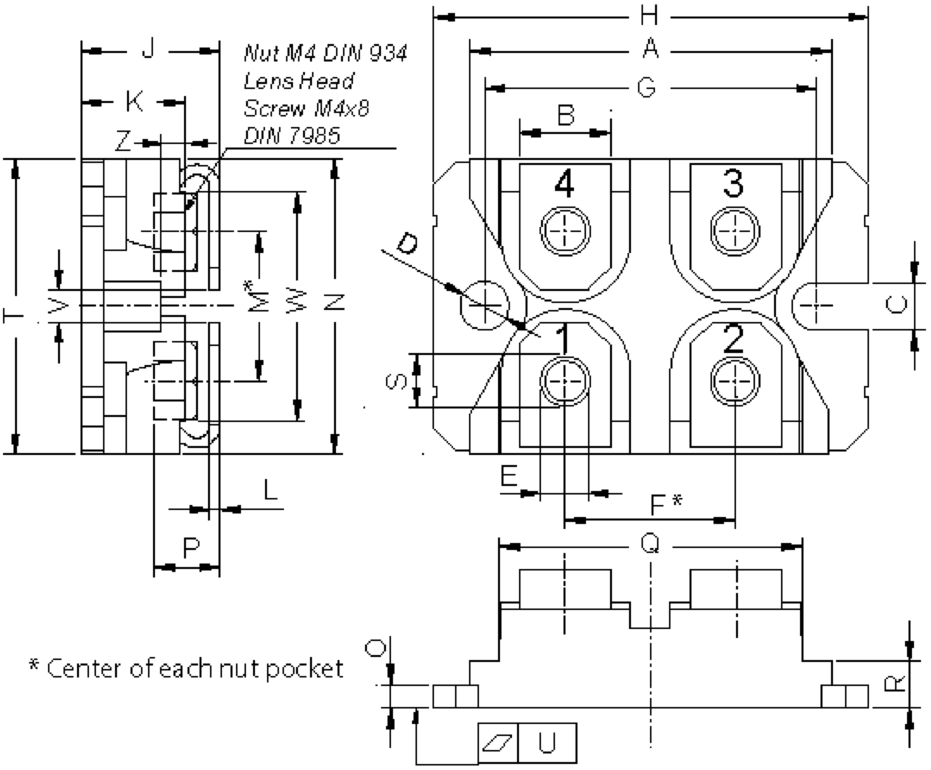
Equivalent Circuits for Simulation

** on die level* $T_{VJ} = 150°C$

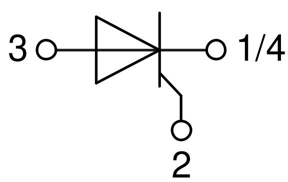


		Thyristor	
$V_{0\ max}$	*threshold voltage*	0.85	V
$R_{0\ max}$	*slope resistance **	3.4	mΩ

Outlines SOT-227B (minibloc)



Dim.	Millimeter		Inches	
	min	max	min	max
A	31.50	31.88	1.240	1.255
B	7.80	8.20	0.307	0.323
C	4.09	4.29	0.161	0.169
D	4.09	4.29	0.161	0.169
E	4.09	4.29	0.161	0.169
F	14.91	15.11	0.587	0.595
G	30.12	30.30	1.186	1.193
H	37.80	38.23	1.488	1.505
J	11.68	12.22	0.460	0.481
K	8.92	9.60	0.351	0.378
L	0.74	0.84	0.029	0.033
M	12.50	13.10	0.492	0.516
N	25.15	25.42	0.990	1.001
O	1.95	2.13	0.077	0.084
P	4.95	6.20	0.195	0.244
Q	26.54	26.90	1.045	1.059
R	3.94	4.42	0.155	0.167
S	4.55	4.85	0.179	0.191
T	24.59	25.25	0.968	0.994
U	-0.05	0.10	-0.002	0.004
V	3.20	5.50	0.126	0.217
W	19.81	21.08	0.780	0.830
Z	2.50	2.70	0.098	0.106



Thyristor

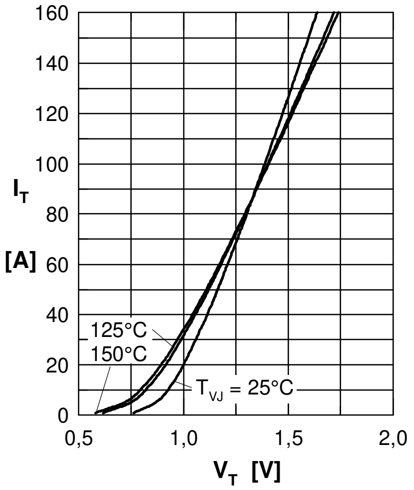


Fig. 1 Forward characteristics

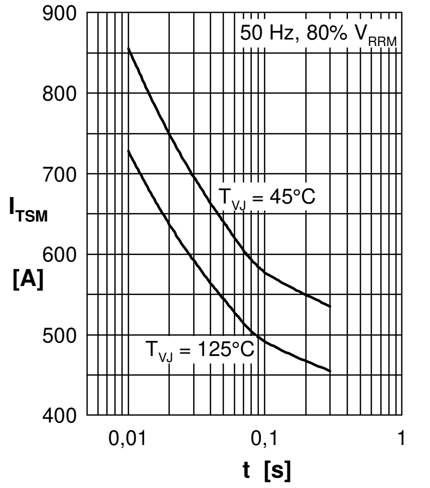


Fig. 2 Surge overload current

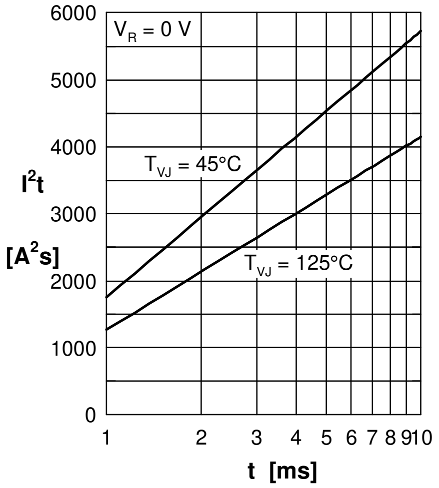


Fig. 3 I^2t versus time (1-10 ms)

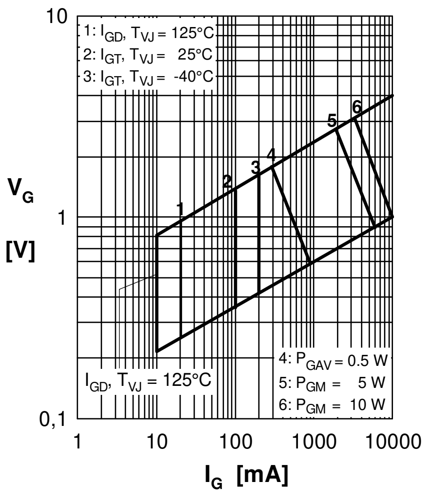


Fig. 4 Gate trigger characteristics

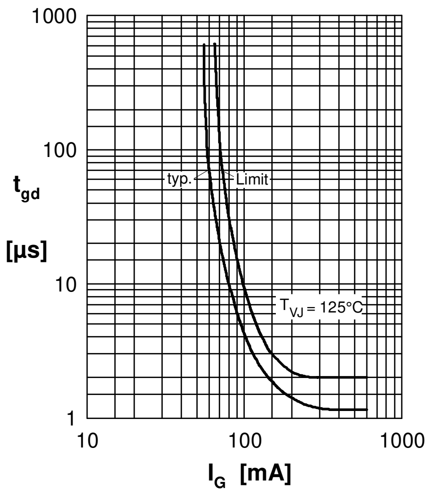


Fig. 5 Gate controlled delay time

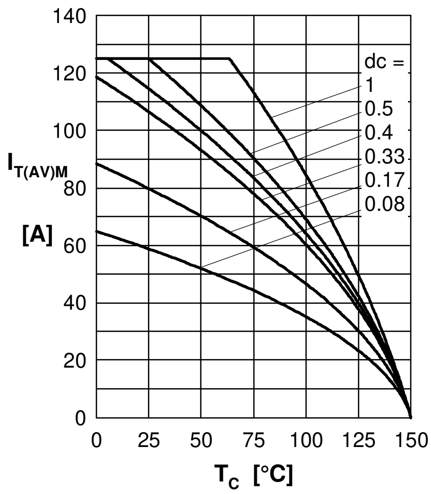


Fig. 6 Max. forward current at case temperature

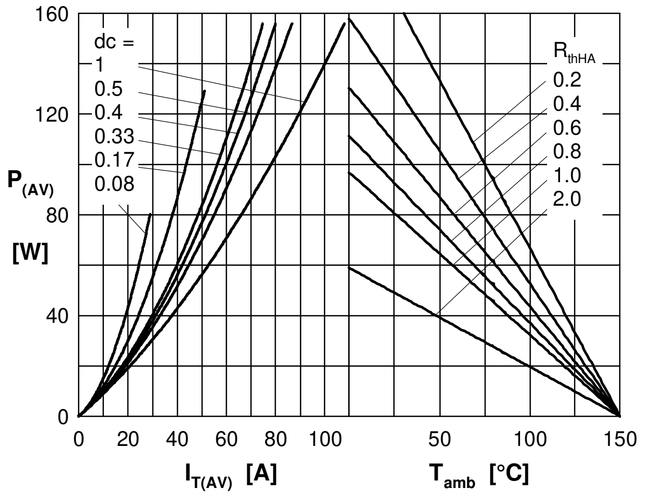


Fig. 7a Power dissipation versus direct output current
Fig. 7b and ambient temperature

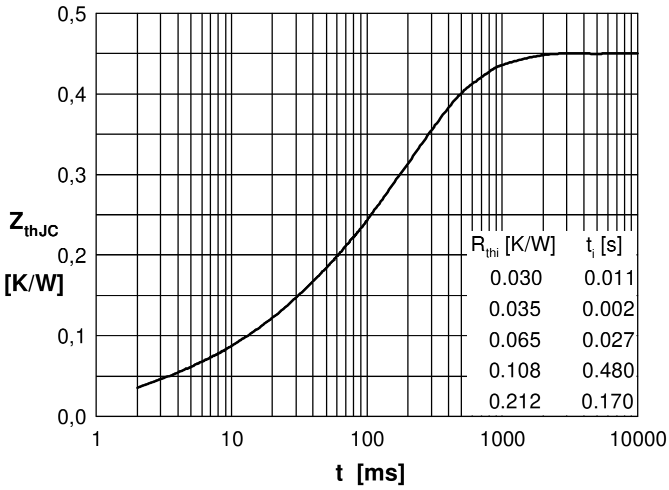


Fig. 8 Transient thermal impedance junction to case